CMHD2003

HIGH VOLTAGE
SWITCHING DIODE

SOD-123 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMHD2003 is a Silicon Switching Diode, manufactured by the epitaxial planar process, epoxy molded in a SOD-123 surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: C03

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	250	V
Continuous Forward Current	I_F	250	mA
Average Rectified Current	I_O	200	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, tp<1s, T_C=25°C	I_{FSM}	1.0	A
Power Dissipation	P_D	400	mW
Operating and Storage			
Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	312.5	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	V_R=200V			100	nA
I_R	V_R=200V, T_C=100°C			15	µA
V_F	I_F=100mA			1.0	V
C_T	V_R=0, f=1 MHz		1.5		pF
t_{rr}	I_F=I_R=30mA, R_L=100Ω, Rec. to 3.0mA			50	ns

R3 (31-October 2002)

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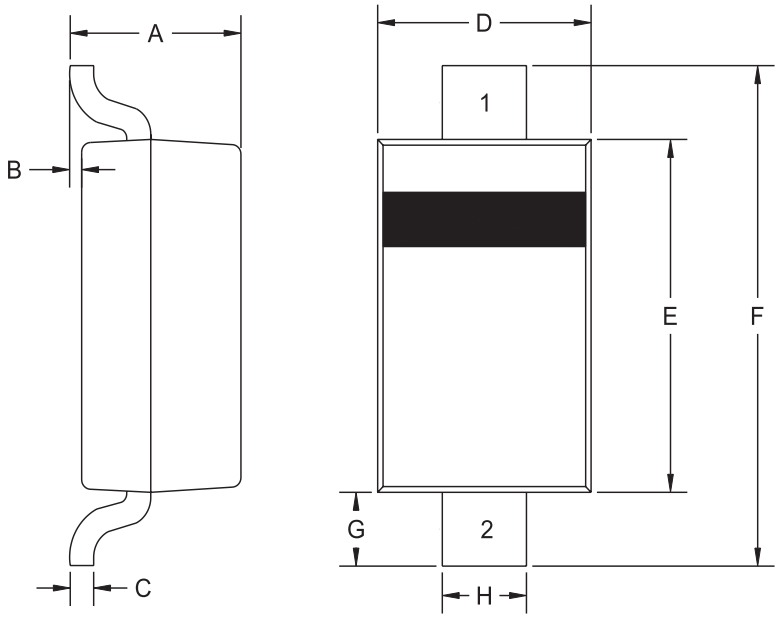
SOD-123 CASE - MECHANICAL OUTLINE



R4

LEAD CODE:
1) CATHODE
2) ANODE

MARKING CODE: C03

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	0.000	0.005	0.00	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.110	2.50	2.80
F	0.142	0.154	3.60	3.90
G	0.016	-	0.40	-
H	0.020	0.028	0.50	0.70

SOD-123 (REV:R4)

R3 (31-October 2002)